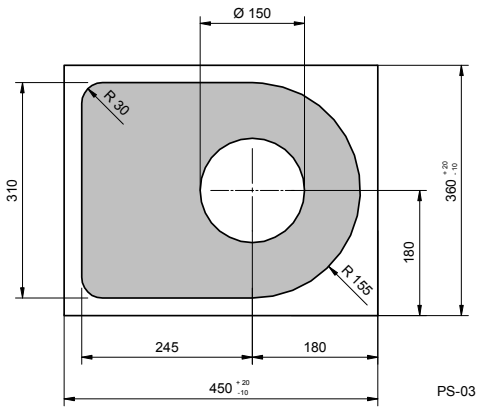
LED - Chip

ELC-650-29-50

Preliminary 10.04.2007 rev. 04/07

Radiation	Type	Technology	Electrodes
Red	Point Source	AlInGaP/GaAs	N (cathode) up



typ. dimensions (µm)

typ. thickness
250 (±20) µm

cathode
gold alloy, 1.5 µm

anode
gold alloy, 0.5 µm

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			35	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 5 mA	V_F		1.85	2.4	V
Reverse voltage	I_R = 10 µA	V_R	5			V
Radiant power*	I_F = 5 mA	Φ_e	100	200		µW
Luminous intensity*	I_F = 5 mA	I_V	5	7		mcd
Peak wavelength	I_F = 5 mA	λ_p	645	655	665	nm
Spectral bandwidth at 50%	I_F = 5 mA	$\Delta\lambda_{0.5}$		20		nm
Switching time	I_F = 5 mA	t_r, t_f		40/30		ns

*Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I_V(typ) [mcd]	V_F(typ) [V]	Quantity
ELC-650-29-50				

Packing: Chips on adhesive film with wire-bond side on top

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